Search Notes

			·	
L Number	Hits	Search Text	DB	Time stamp
_	0	upstanding adj pillar same etch\$3 and gate and pore	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15 00:12
-	0	upstanding adj pillar and etch\$3 and gate and pore	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	224	upstanding adj pillar	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	19	upstanding adj pillar and etch\$3	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15 00:13
-	8	upstanding adj pillar and etch\$3 and gate	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	17	upstanding with pillar and etch\$3 and gate	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	62	pillar and etch\$3 and gate and pore	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	3	pillar and etch\$3 and gate same pore	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/04/15 00:31
_	5	pillar and gate same pore	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	218	channel and gate same pore	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	102	channel and gate with pore	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	5	channel and gate with pore and stack	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/15
-	69	pore same transistor and channel	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/11 22:20

-	3	pore same transistor and channel and gate	USPAT;	2004/06/11
		and etch\$3 and pillar	US-PGPUB;	22:41
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	555	(438/268).CCLS.	USPAT;	2004/06/11
		(100, 200, 10022)	US-PGPUB;	22:28
			EPO; JPO;	22.20
			DERWENT;	
İ				
	1684	(438/270).CCLS.	IBM_TDB USPAT;	2004/06/11
-	1604	(430/2/0).CCL3.	US-PGPUB;	22:28
				22:20
			EPO; JPO;	ļ
			DERWENT;	
	67.6	(055 (000)	IBM_TDB	
-	676	(257/382).CCLS.	USPAT;	2004/06/11
			US-PGPUB;	22:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	288	(257/383).CCLS.	USPAT;	2004/06/11
			US-PGPUB;	22:28
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	534	(257/302).CCLS.	USPAT;	2004/06/11
	33.	(2377 302): Gelb:	US-PGPUB;	22:28
			EPO; JPO;	22.20
			DERWENT;	
	796	/420/107) GGT G	IBM_TDB	2024/26/11
_	/96	(438/197).CCLS.	USPAT;	2004/06/11
			US-PGPUB;	22:34
			EPO; JPO;	
			DERWENT;	
	_	,	IBM_TDB	
-	0	nanopillar and transistor and nanppore	USPAT;	2004/06/11
			US-PGPUB;	22:35
			EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
-	1	nanopillar and transistor and nanopore	USPAT;	2004/06/11
		-	US-PGPUB;	22:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	7	nanopillar and transistor	USPAT;	2004/06/11
		•	US-PGPUB;	22:37
.			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	52	pore same transistor and channel and gate	USPAT;	2004/06/11
	52	and etch\$3		· · ·
		and econys	US-PGPUB;	22:41
]			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0004/05/55
-	3	pore same transistor and channel and gate	USPAT;	2004/06/11
		and etch\$3 and pillar	US-PGPUB;	22:41
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	